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Edwards STP-iXR2206

Technical Specifications

Inlet flange size	VG250/ISO250F/DN250CF	
Backing port size	KF40	
Pumping speed N_2	2200	litres/second
Pumping speed H_2	1350	litres/second
Pumping speed Ar	2000	litres/second
Compression ratio N_2/H_2	$>10^8/1 \times 10^3$	
Ultimate pressure	10^{-7} (10^{-9})	Pa (Torr)
Allowable backing pressure	266 (2)	Pa (Torr)
Max gas flow N_2 (water cooled only) *1	3100 (5.24)	sccm (Pa m^3/sec)
Max gas flow Ar (water cooled only) *1	1700 (2.87)	sccm (Pa m^3/sec)
Rated speed	36500	rpm
Start time	≤10	minutes
Mounting position	Any orientation	
Input voltage	200-240	V
Max input power	750	VA
Weight	48	kg

**1 The maximum gas flow quoted applies under the conditions that N_2 gas is pumped continuously with water cooling temperature under 25 degree C, with N_2 purge and a backing pump 10,000 l/min size or larger used. The value is changed if operated under different conditions*

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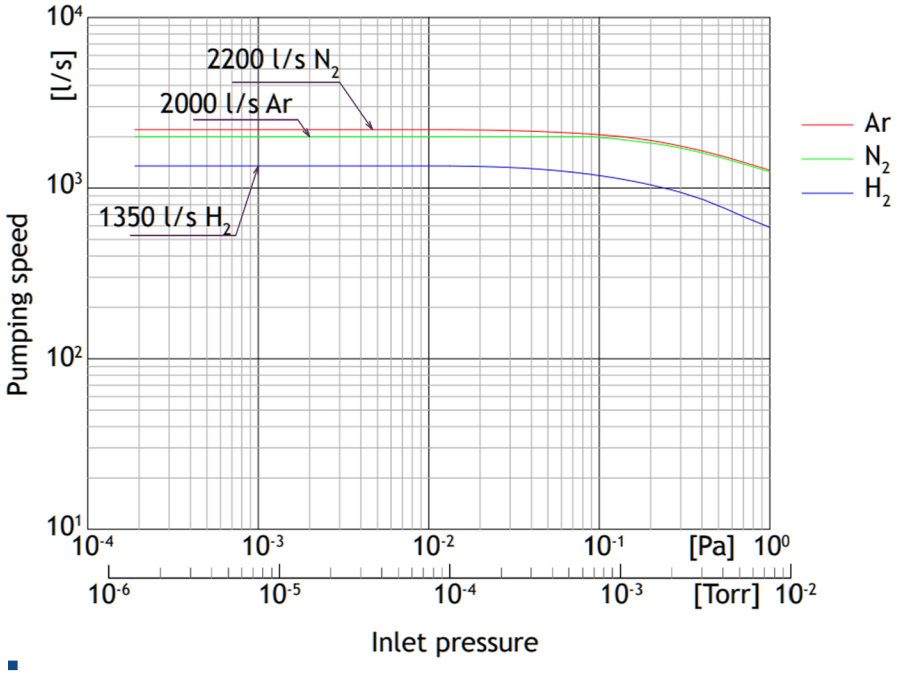
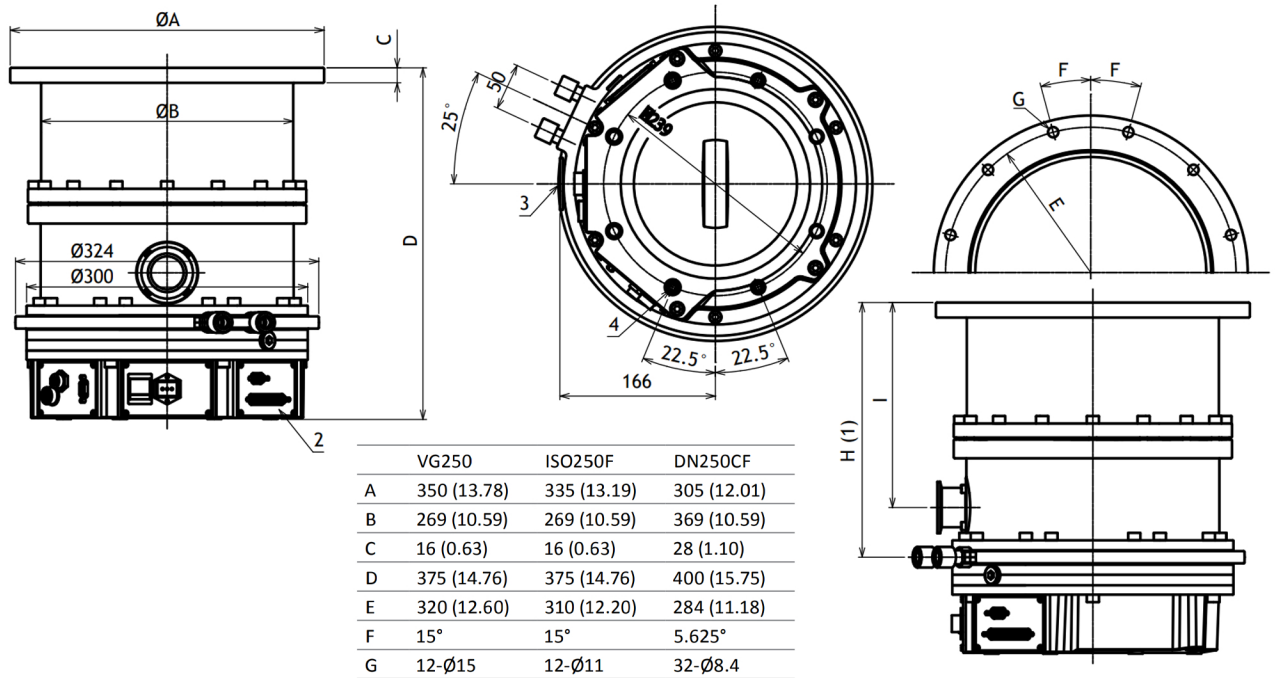
Pumping Curves



Dimensions



	VG250	ISO250F	DN250CF
A	350 (13.78)	335 (13.19)	305 (12.01)
B	269 (10.59)	269 (10.59)	369 (10.59)
C	16 (0.63)	16 (0.63)	28 (1.10)
D	375 (14.76)	375 (14.76)	400 (15.75)
E	320 (12.60)	310 (12.20)	284 (11.18)
F	15°	15°	5.625°
G	12-Ø15	12-Ø11	32-Ø8.4
H	271 (10.67)	271 (10.67)	396 (15.59)
I	219 (8.62)	219 (8.62)	244 (9.61)

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Features & Benefits

- fully integrated onboard controller
- revolutionary new rotor design enables use of smaller platform
- compact design with low input power
- high performance with installation flexibility
- low power consumption
- low cost of ownership
- water & dust proof specification is provided as standard
- various comunication options

Applications

- plasma etch • ECR etch • film deposition • sputtering • ion implantation source • beam line pumping end station • MBE • diffusion • photo resist stripping • crystal, epitaxial growth • wafer inspection • load lock chambers • surface analysis • mass spectrometry • electron microscopy • high energy physics • radioactive applications